

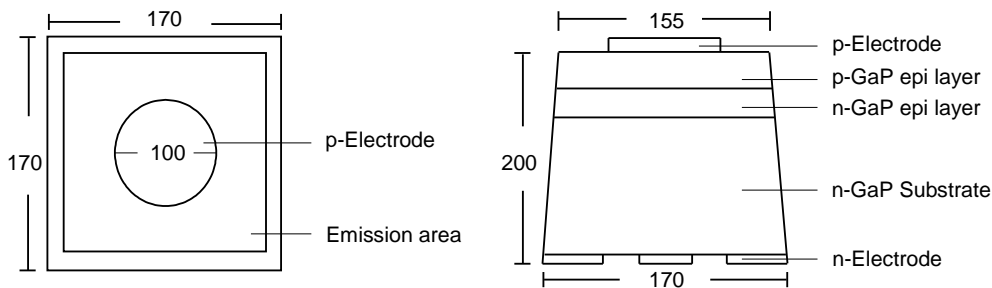
Features :

- GaP/GaP Epi Wafer

Typical Applications :

- Lamp
- SMD

Outline Dimensions : (Unit: μm)



Physical Structure :

Chip dimension	Chip size	170 μm x 170 μm
	Thickness	200 μm
	Emission area	155 μm
	Bonding pad	100 μm
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	1.90	2.30	2.40	V
Reverse Current	I_R	$V_R = 5 \text{ V}$	-	-	10	μA
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	568	-	nm
	Hue		569	572	574	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	30	-	nm
Luminous Intensity	I_V	$I_F = 20 \text{ mA}$	6.0	-	-	mcd